



# DMP10H400SE

#### 100V P-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C	
-100V	250mΩ @ $V_{GS}$ = -10 $V$	-2.3A	
-1007	300mΩ @ V <sub>GS</sub> = -4.5V	-2.1A	

# **Description**

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

### **Applications**

- Motor Control
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply

### **Features and Benefits**

- Low Gate Drive
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

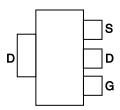
#### **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Lead Frame.
  Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)

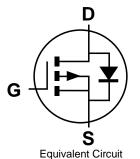
SOT223



Top View



Pin Out - Top View



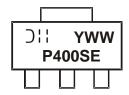
### Ordering Information (Note 4)

Part Number	Qualification	Case	Packaging	
DMP10H400SE-13	Standard	SOT223	2,500 / Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



O!! = Manufacturer's Marking P400SE = Marking Code YWW = Date Code Marking Y or Y= Year (ex: 4 = 2014) WW = Week (01 to 53)



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Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			$V_{DSS}$	-100	V
Gate-Source Voltage	$V_{GSS}$	±20	V		
Continuous Drain Current (Note 5) V <sub>GS</sub> = -10V	Steady State	$T_C = +25$ °C $T_A = +25$ °C	I <sub>D</sub>	-6.0 -2.3	А
Maximum Body Diode Forward Current (Note 5)	Is	-1.9	Α		
Pulsed Drain Current (380μs Pulse, Duty Cycle = 1%	I <sub>DM</sub>	-10	Α		

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	D	2.0	W
Total Fower Dissipation (Note 5)	T <sub>A</sub> = +70°C	P <sub>D</sub>	1.3	
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	62	°C/W	
Total Power Dissipation (Note 5) $T_C = +25^{\circ}C$		P <sub>D</sub>	13.7	W
Thermal Resistance, Junction to Case (Note 5)	R <sub>0JC</sub>	9.1	°C/W	
Operating and Storage Temperature Range	$T_{J}, T_{STG}$	-55 to +150	°C	

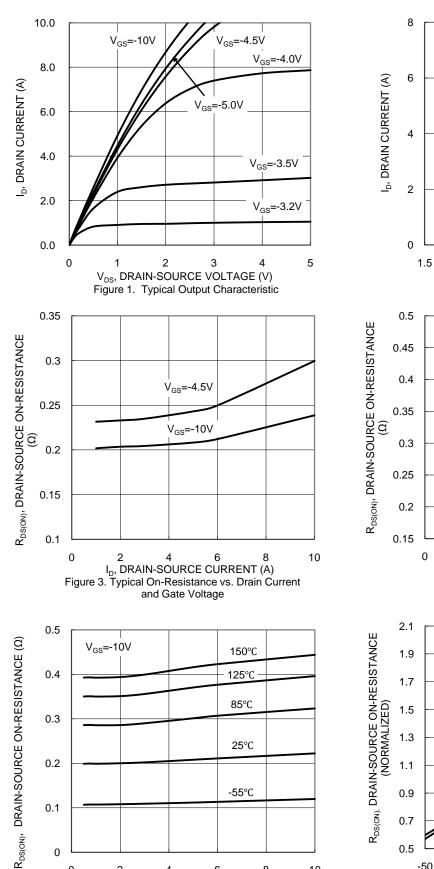
## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	$BV_{DSS}$	-100	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = -80V, V_{GS} = 0V$
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1.0	-2.2	-3.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
Static Drain-Source On-Resistance		_	203	250	mΩ	$V_{GS} = -10V, I_D = -5A$
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	241	300	1115.2	$V_{GS} = -4.5V, I_D = -5A$
Diode Forward Voltage	$V_{SD}$	_	-0.9	-1.2	V	$V_{GS} = 0V, I_{S} = -5A$
DYNAMIC CHARACTERISTICS (Note 7)	DYNAMIC CHARACTERISTICS (Note 7)					
Input Capacitance	Ciss	_	1239	_		
Output Capacitance	Coss	_	42	_	pF	$V_{DS} = -25V$ , $V_{GS} = 0V$ , $f = 1.0MHz$
Reverse Transfer Capacitance	C <sub>rss</sub>	_	28	_		
Gate Resistance	$R_{G}$	_	13	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge (V <sub>GS</sub> = -4.5V)	$Q_g$	_	8.4	_		
Total Gate Charge (V <sub>GS</sub> = -10V)	$Q_g$	_	17.5	_	nC	V <sub>DS</sub> = -60V. I <sub>D</sub> = -5A
Gate-Source Charge	$Q_{gs}$	_	2.8	_	IIC	VDS = -00V, ID = -5A
Gate-Drain Charge	$Q_{gd}$	_	3.2	_		
Turn-On Delay Time	t <sub>D(ON)</sub>	_	9.1	_		
Turn-On Rise Time	t <sub>R</sub>	_	14.9	_		$V_{DD} = -50V, R_G = 9.1\Omega, I_D = -5A$
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	57.4	_	ns	
Turn-Off Fall Time	t <sub>F</sub>		34.4	—		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	25.2	_	ns	$V_{GS} = 0V$ , $I_S = -5A$ , $dI/dt = 100A/\mu s$
Body Diode Reverse Recovery Charge	$Q_{RR}$	_	24.5		nC	$V_{GS} = 0V$ , $I_S = -5A$ , $dI/dt = 100A/\mu s$

Notes:

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.6. Short duration pulse test used to minimize self-heating effect.
- 7. Guaranteed by design. Not subject to production testing.





6

I<sub>D</sub>, DRAIN CURRENT (A)

Figure 5. Typical On-Resistance vs. Drain Current and

Junction Temperature

8

125°C 85°C 150°C -55°C 2 2.5 3 3.5 4 4.5 V<sub>GS</sub>, GATE-SOURCE VOLTAGE (V) Figure 2. Typical Transfer Characteristic  $I_{D} = -5.0A$ 8 12 20 16 V<sub>GS</sub>, GATE-SOURCE VOLTAGE (V) Figure 4. Typical Transfer Characteristic  $V_{GS}$ =-10V,  $I_{D}$ =-5.0A  $V_{GS}$ =-4.5V,  $I_{D}$ =-5.0A -50 -25 0 25 50 75 100 125 150

T<sub>J</sub>, JUNCTION TEMPERATURE (°C)

Figure 6. On-Resistance Variation with Junction

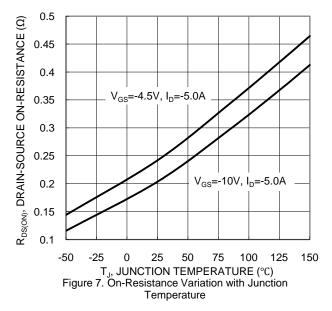
Temperature

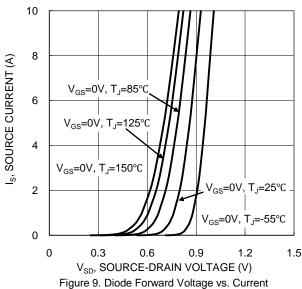
 $V_{DS}$ =-5V

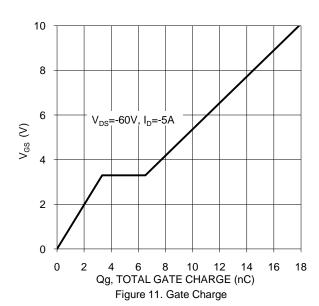
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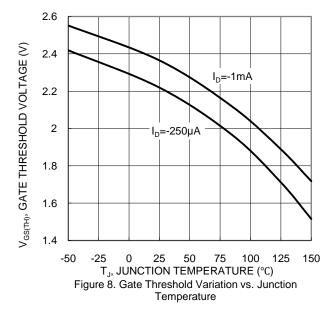
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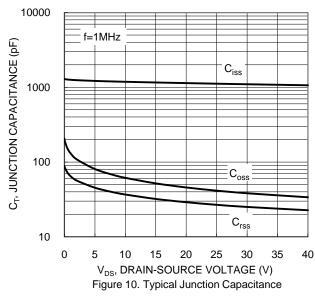


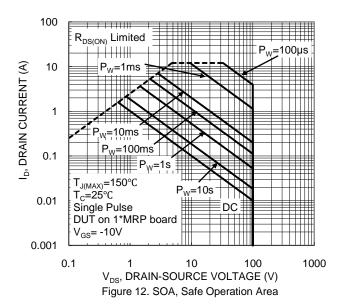




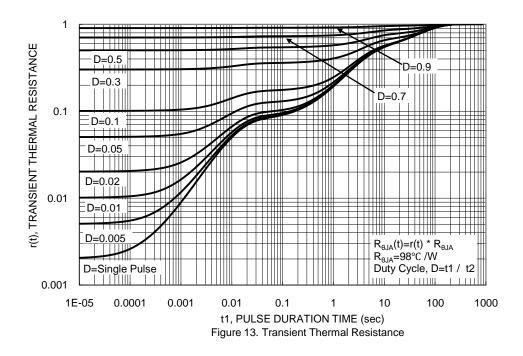






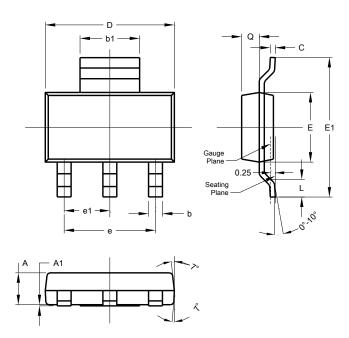






# **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

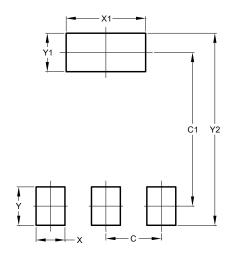


SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
C	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
q	0.84	0.94	0.89		
All Dimensions in mm					



### Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
Y2	8.00

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